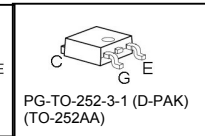
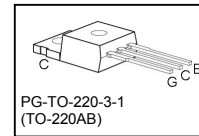
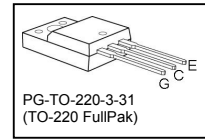
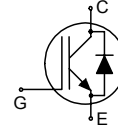


LightMOS Power Transistor

- New high voltage technology designed for ZVS-switching in lamp ballasts
- IGBT with integrated reverse diode
- 4A current rating for reverse diode
- Up to 10 times lower gate capacitance than MOSFET
- Avalanche rated
- 150°C operating temperature
- FullPak isolates 2.5 kV AC (1 min.)
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹ for target applications



Type	V _{CE}	I _C	V _{CE(sat)} , T _J =25°C	T _{J,max}	Marking	Package	Ordering Code
ILA03N60	600V	3.0A	2.9V	150°C	L03N60	PG-TO-220-3-31	Q67040-S4626
ILP03N60	600V	3.0A	2.9V	150°C	L03N60	PG-TO-220-3-1	Q67040-S4628
ILD03N60	600V	3.0A	2.9V	150°C	L03N60	PG-TO-252-3-1	Q67040-S4625

Maximum Ratings

Parameter	Symbol	Value		Unit
		ILA03N60	Others	
Collector-emitter voltage	V _{CE}	600		V
DC collector current	I _C	T _C = 25°C	3	A
		T _C = 100°C	2.2	
Pulsed collector current, t _p limited by T _{J,max} , t _p < 10 ms	I _{C,puls}	9		
Pulsed collector current, t _p limited by T _{J,max}		5.5		
Diode forward current	I _F	T _C = 25°C	4	4
		T _C = 100°C	2.2	
Diode pulsed current, t _p limited by T _{J,max} , t _p < 10 ms	I _{F,puls}	9		
Diode pulsed current, t _p limited by T _{J,max}		5.5		
Avalanche energy, single pulse I _C =0.4A, V _{CE} =50V	E _{AS}	0.32		mJ
Gate-emitter voltage	V _{GE}	±30		V
Reverse diode dv/dt I _C ≤ 3A, V _{CE} ≤ 450V, T _{J,max} ≤ 150°C	dv/dt	1 ²		V/ns
Power dissipation (T _C = 25°C)	P _{tot}	16.5	27	W
Operating junction and storage temperature	T _{stg}	-55...+150		°C
Soldering temperature PG-TO-252: reflow soldering MSL3 Others: wavesoldering, 1.6 mm (0.063 in.) from case for 10s	T _s	260		
		260		

¹ J-STD-020 and JESD-022

² Reverse diode of transistor is commutated with same device according to figure C. With application relevant values I_C ≤ 1.5A, C_{Snubber} = 1 nF and R_G ≥ 50Ω, dv/dt of the reverse diode is within its specification.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}	PG-TO-220-3-31	7.6	K/W
		Other packages	4.7	
Diode thermal resistance, junction – case	R_{thJCD}	PG-TO-220-3-31	12	
		Other packages	10	
Therm. resistance, junction – ambient	R_{thJA}	PG-TO-220-3-31	65	
		PG-TO-220-3-1	62	
SMD version, device on PCB: @ min. footprint @ 6cm ² cooling area ¹	R_{thJA}	PG-TO-252-3-1	75	
			50	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.5mA$	600	-	-	V
Collector-emitter avalanche breakdown voltage	$V_{(BR)CE}$	$V_{GS}=0V; I_C=0.4A$	-	850	-	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=10V, I_C=3.0A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	2.3	2.9	
			-	2.7		
		$V_{GE}=10V, I_C=0.8A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	1.5	-	
			-	1.5	-	
Diode forward voltage	V_F	$V_{GE}=0V, I_F=3.0A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	1.5	1.8	
			-	1.6		
		$V_{GE}=0V, I_F=0.8A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	1.0	-	
			-	1.0	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=30\mu A, V_{CE}=V_{GE}$	2.1	3.0	3.9	V

¹ Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristic, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified continued

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600\text{V}, V_{GE}=0\text{V}$ $T_j=25\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	-	1	20	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0\text{V}, V_{GE}=20\text{V}$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20\text{V}, I_C=3.0\text{A}$	-	1.5	-	S

Capacities, Gate Charge, at $T_j=25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{CE}=25\text{V},$	-	110	-	pF
Output capacitance	C_{oss}	$V_{GE}=0\text{V},$	-	6	-	
Reverse transfer capacitance	C_{rfs}	$f=1\text{MHz}$	-	4	-	
Effective Output Capacitance (Energy related)	$C_{o(er)}$	$V_{GE}=0\text{V},$ $V_{CE}=0\text{V to }480\text{V}$		3.7		pF
Gate to emitter charge	Q_{GE}	$V_{CE}=400\text{V},$ $I_C=3.0\text{A},$ $V_{GE}=10\text{V}$	-	1	-	nC
Gate to collector charge	Q_{GC}		-	5.5	-	
Gate total charge	Q_G		-	8.5	-	
Gate plateau voltage	V_m		-	6.5	-	
Gate to emitter charge	Q_{GE}	$V_{CE}=400\text{V},$ $I_C=0.8\text{A},$ $V_{GE}=10\text{V}$	-	0.5	-	nC
Gate to collector charge	Q_{GC}		-	4.0	-	
Gate total charge	Q_G		-	8	-	
Gate plateau voltage	V_m		-	3.5	-	

Switching Characteristic, Inductive Load, at $T_j=25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$V_{CC}=400\text{V},$ $I_C=0.8\text{A},$ $V_{GE}=0/10\text{V},$ $R_G=60\Omega,$ $C_{S\text{snubber}}=0\text{nF}$ ($C_{S\text{snubber}}$: Snubber capacitor)	-	15	-	ns
Rise time	t_r		-	35	-	
Turn-off delay time	$t_{d(off)}$		-	100	-	
Fall time	t_f		-	100	-	
Turn-on energy	E_{on}^4	$C_{S\text{snubber}}=1\text{nF}$	-	12	-	μJ
Turn-off energy	E_{off}		-	20	-	
Turn-off energy	E_{off}		-	8	-	

⁴ E_{on} includes SDP04S60 diode commutation losses

Switching Characteristic, Inductive Load, at $T_j=150\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$V_{CC}=400\text{V}$, $I_C=0.8\text{A}$, $V_{GE}=0/10\text{V}$, $R_G=60\Omega$, $C_{Snubber}=0\text{nF}$ ($C_{Snubber}$: Snubber capacitor)	-	20	-	ns
Rise time	t_r		-	45	-	
Turn-off delay time	$t_{d(off)}$		-	120	-	
Fall time	t_f		-	120	-	
Turn-on energy	E_{on}^3	$C_{Snubber}=1\text{nF}$	-	15	-	μJ
Turn-off energy	E_{off}		-	28	-	
Turn-off energy	E_{off}		-	12	-	

Switching Characteristic, Inductive Load, at $T_j=25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse diode Characteristic (switching in half bridge configuration with same transistor according to figure C)						
Reverse recovery time	t_{rr}	$V_R=400\text{V}$, $I_F=0.8\text{A}$, $V_{GE}=0/10\text{V}$, $R_G=80\Omega$	-	90	-	ns
Reverse recovery charge	Q_{rr}		-	0.27	-	μC
Peak reverse recovery current	I_{rrm}		-	5.5	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	300	-	A/ μs
Reverse recovery time	t_{rr}	$V_R=400\text{V}$, $I_F=3\text{A}$, $V_{GE}=0/10\text{V}$, $R_G=80\Omega$	-	250	-	ns
Reverse recovery charge	Q_{rr}		-	0.75	-	μC
Peak reverse recovery current	I_{rrm}		-	8	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	300	-	A/ μs

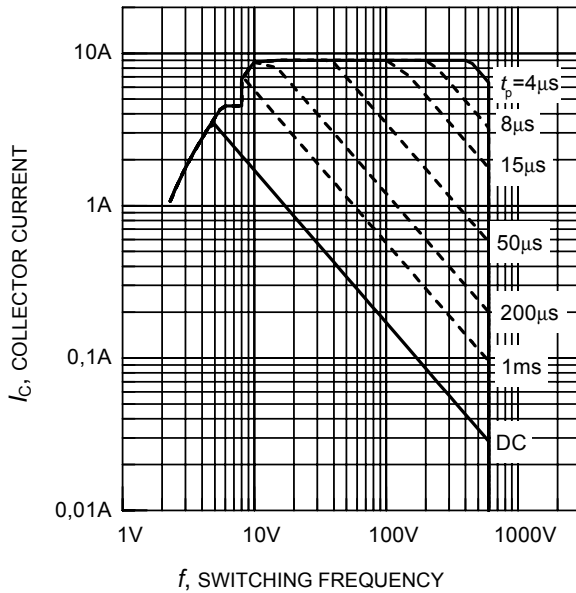


Figure 1: Safe operating area (FullPak)
($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)

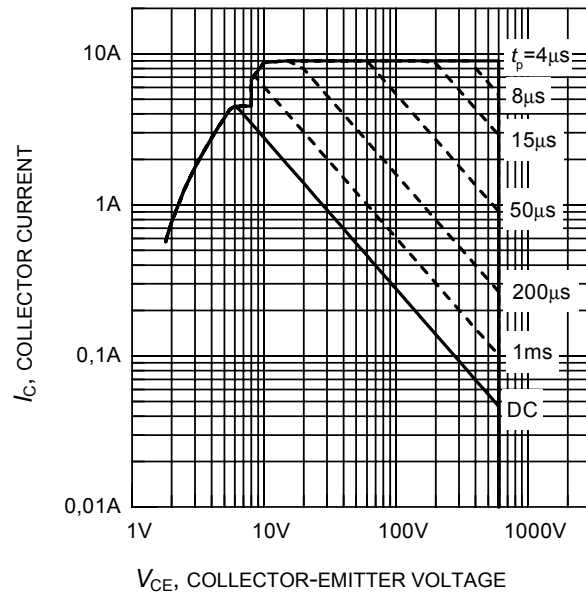


Figure 2: Safe operating area (Other Packages)
($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)

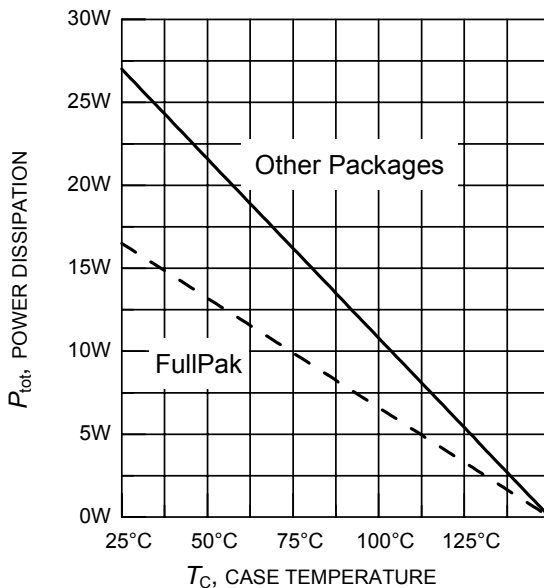


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 150^\circ\text{C}$)

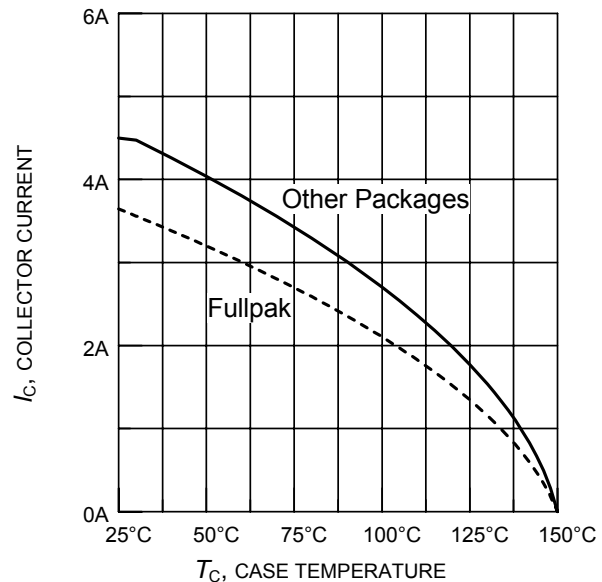


Figure 4. Collector current as a function of case temperature
($V_{GE} \leq 10\text{V}$, $T_j \leq 150^\circ\text{C}$)

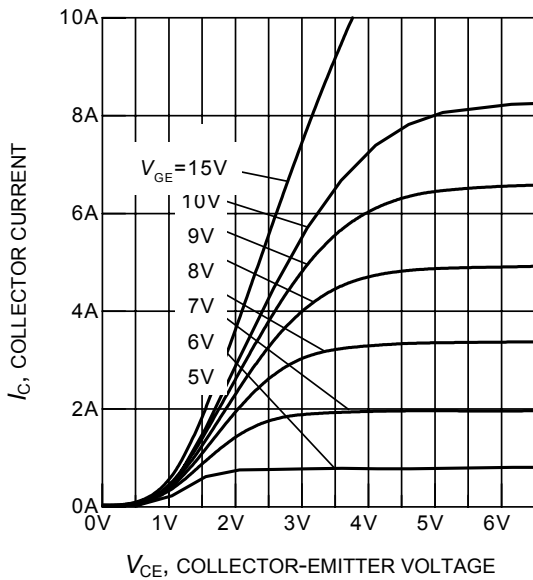


Figure 5. Typical output characteristics
($T_j = 25^\circ\text{C}$)

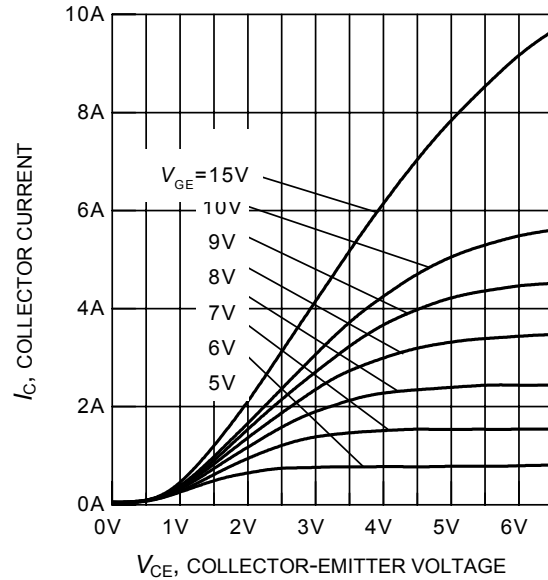


Figure 6. Typical output characteristics
($T_j = 150^\circ\text{C}$)

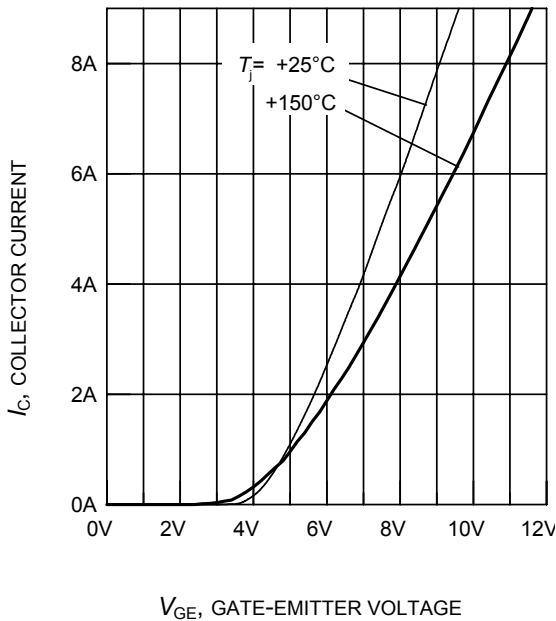


Figure 7. Typical transfer characteristics
($V_{CE} = 20\text{V}$)

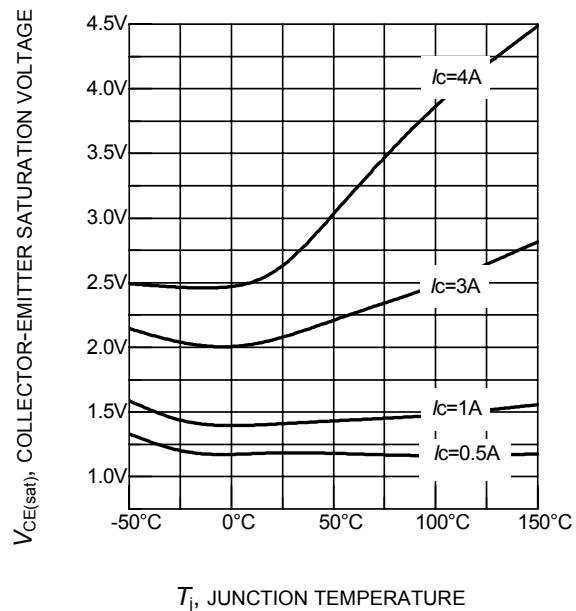


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 10\text{V}$)

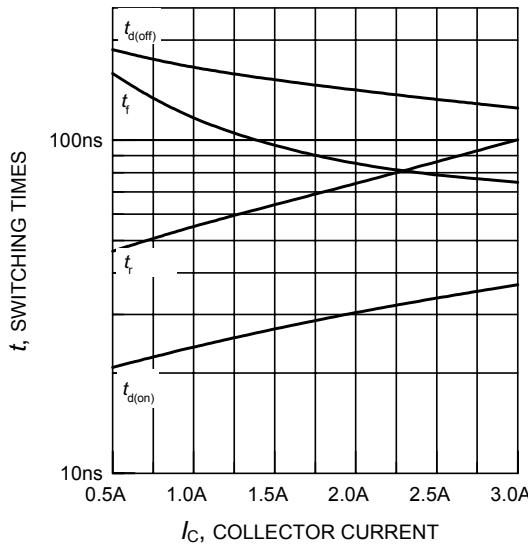


Figure 9. Typical switching times as a function of collector current
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $R_G = 80\Omega$, Dynamic test circuit in Figure E)

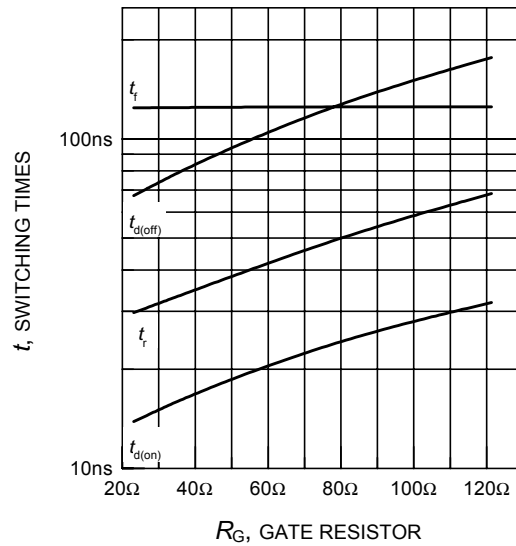


Figure 10. Typical switching times as a function of gate resistor
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $I_C = 1\text{A}$, Dynamic test circuit in Figure E)

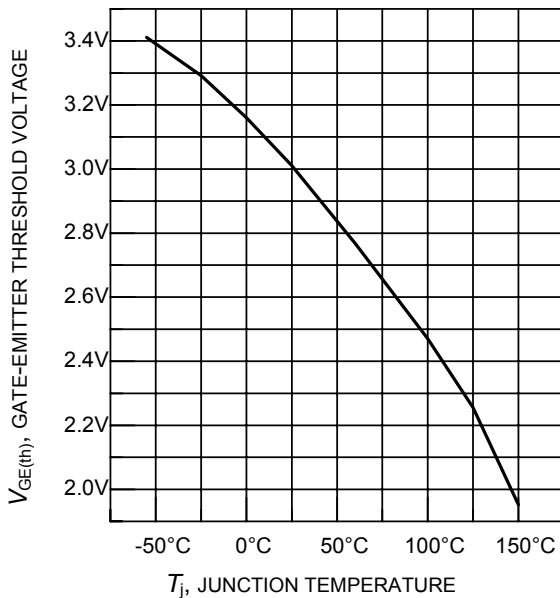


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
($I_C = 30\mu\text{A}$)

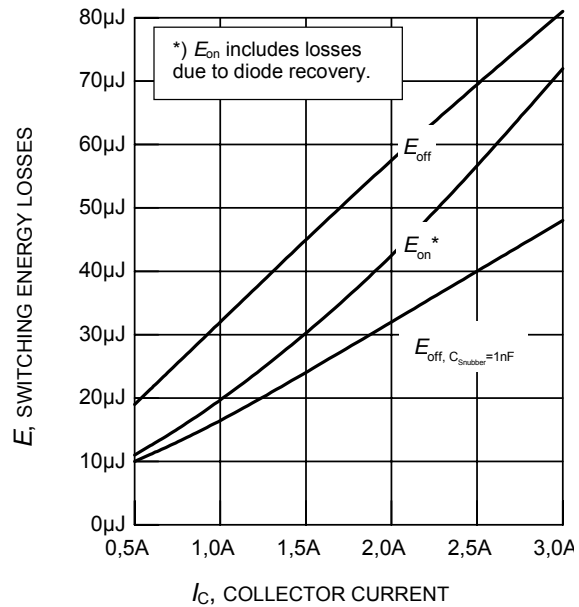


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $R_G = 80\Omega$, $C_{Snubber} = 0/1\text{nF}$, Dynamic test circuit in Figure E)

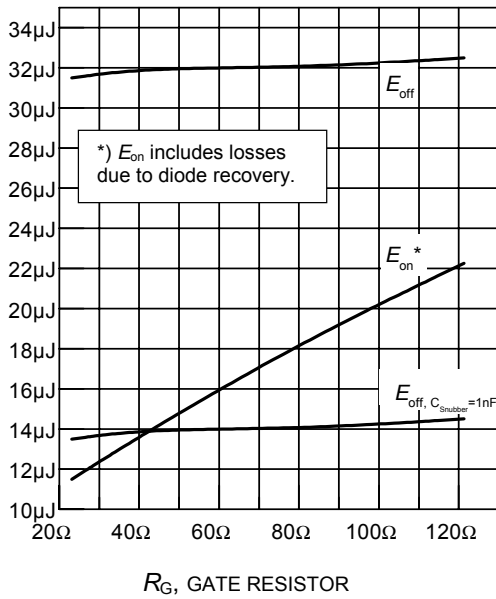


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $I_C = 1\text{A}$, $C_{Snubber} = 0/1\text{nF}$
Dynamic test circuit in Figure E)

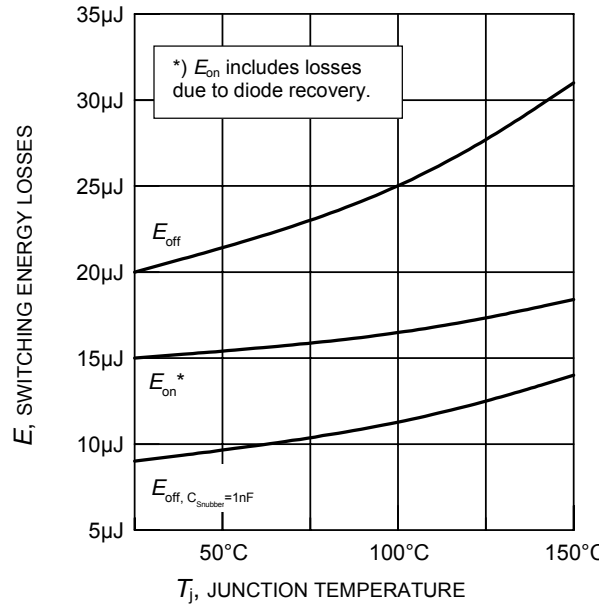


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $I_C = 1\text{A}$, $R_G = 80\Omega$, $C_{Snubber} = 0/1\text{nF}$
Dynamic test circuit in Figure E)

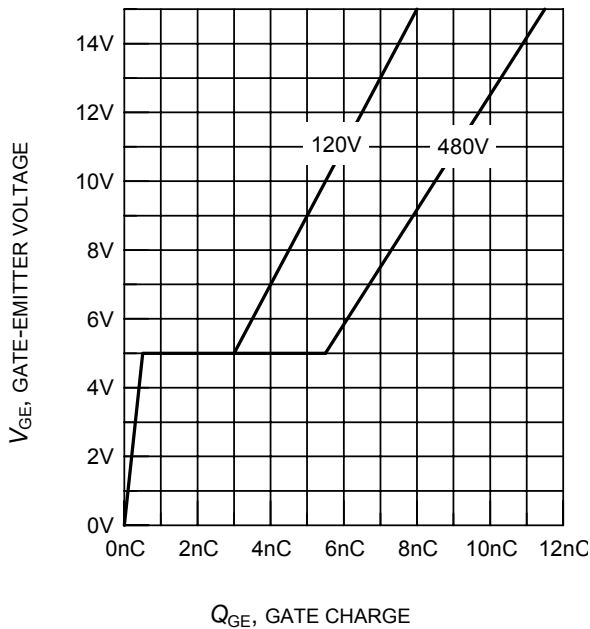


Figure 16. Typical gate charge
($I_C = 0.8\text{A}$)

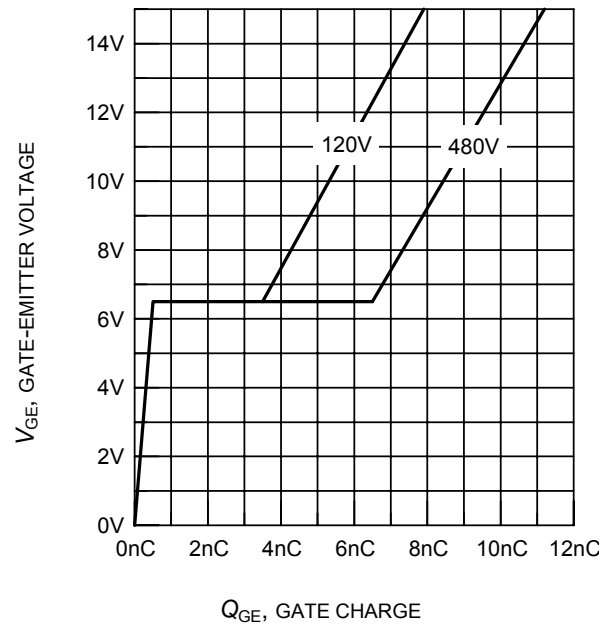


Figure 17. Typical gate charge
($I_C = 3\text{A}$)

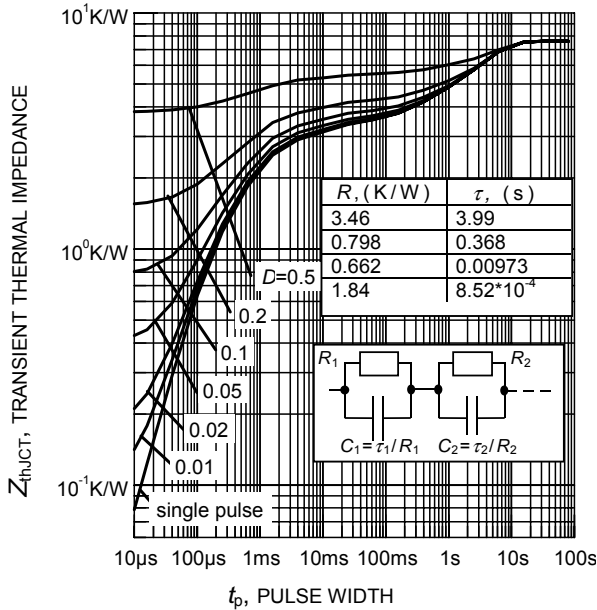


Figure 18: IGBT transient thermal impedance as a function of pulse width (FullPak)
($D = t_p / T$)

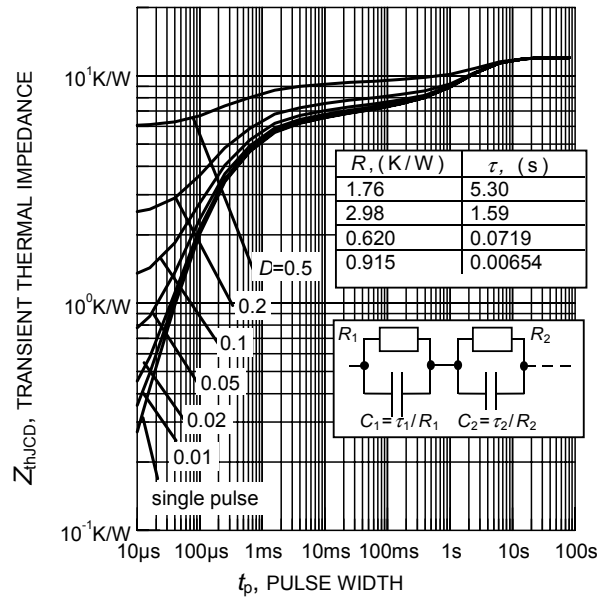


Figure 19: Diode transient thermal impedance as a function of pulse width (FullPak)
($D = t_p / T$)

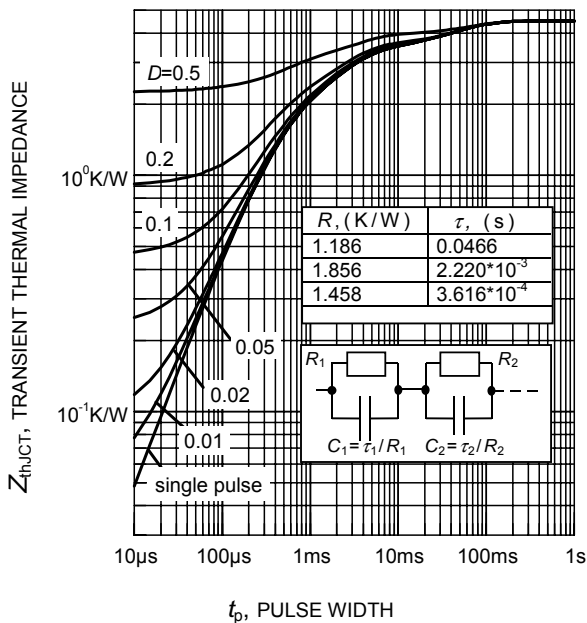


Figure 20: IGBT transient thermal impedance as a function of pulse width (Other Packages)
($D = t_p / T$)

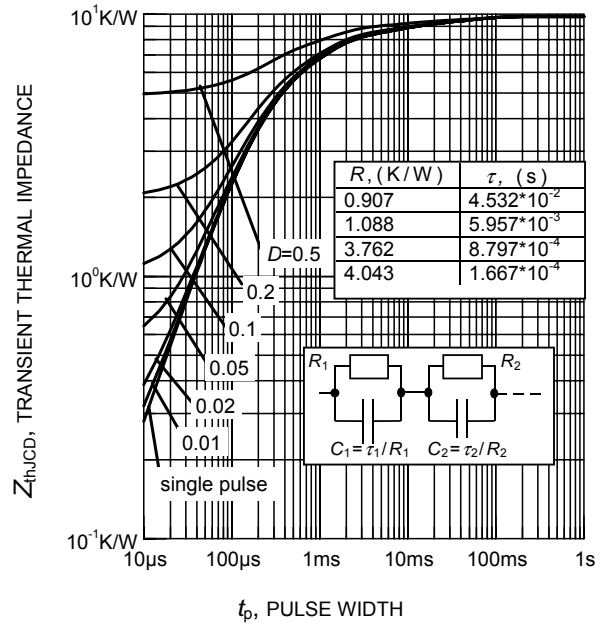


Figure 21: Diode transient thermal impedance as a function of pulse width (Other Packages)
($D = t_p / T$)

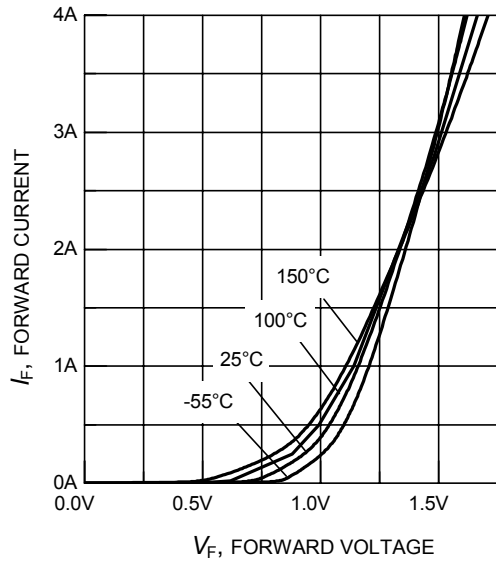


Figure 20. Typical diode forward current as a function of forward voltage

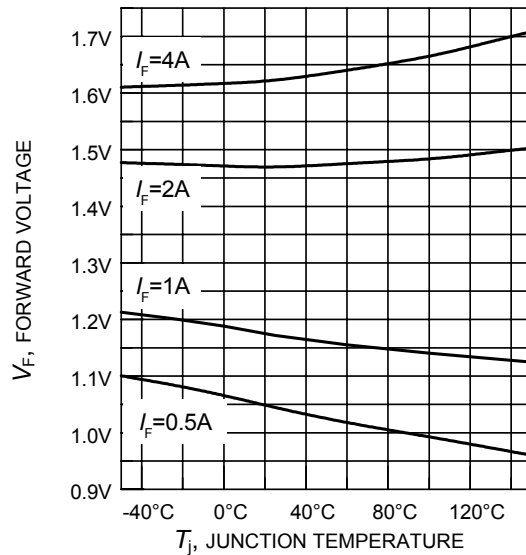


Figure 21. Typical diode forward voltage as a function of junction temperature

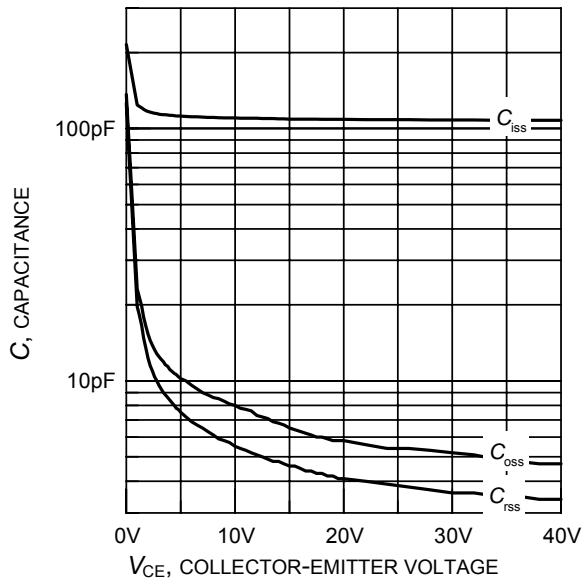


Figure 19. Typical capacitance as a function of collector-emitter voltage
($V_{GE} = 0V$, $f = 1MHz$)

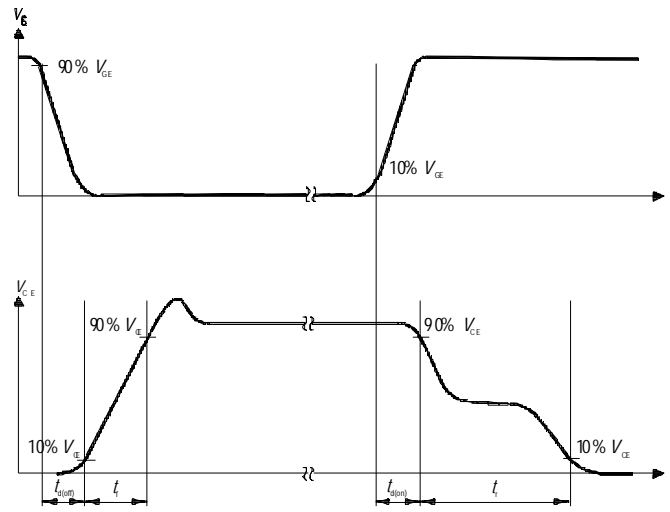


Figure A. Definition of switching times

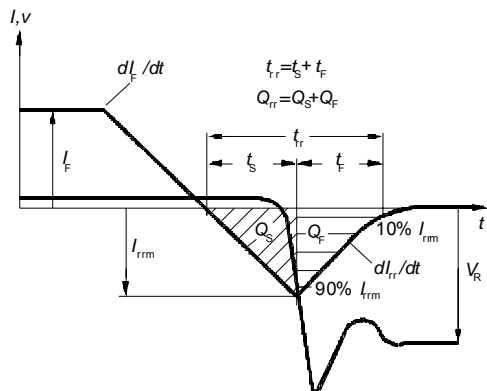


Figure B. Definition of diodes switching characteristics

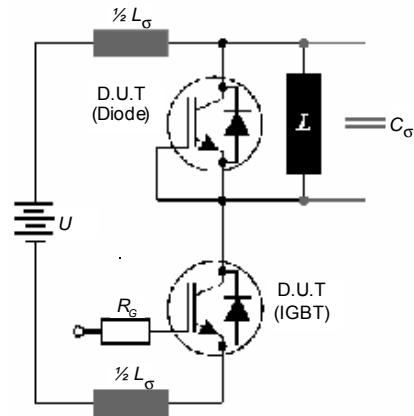
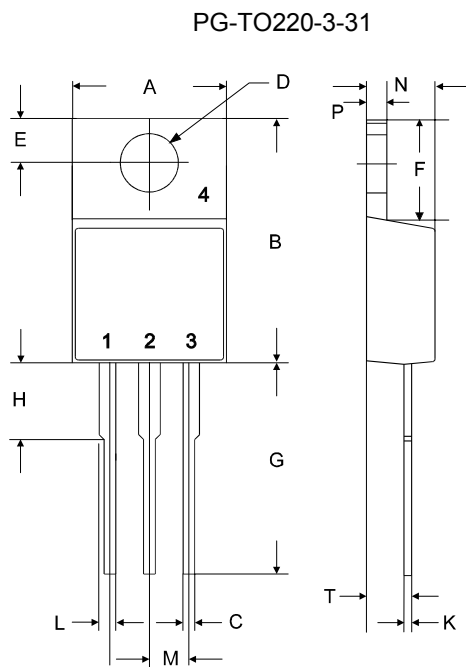


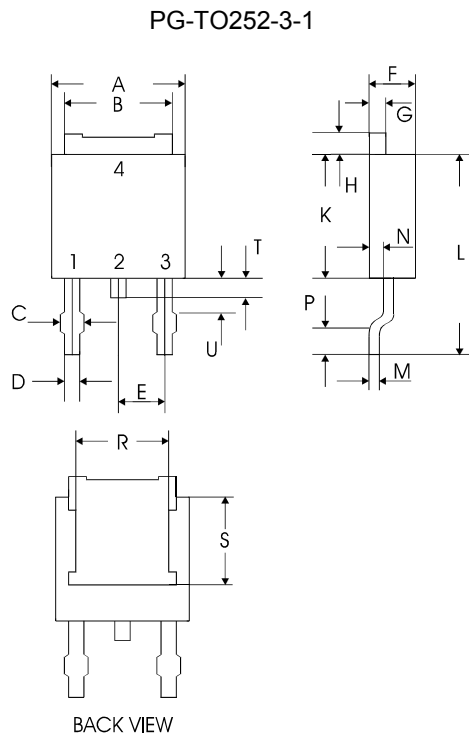
Figure C. Dynamic test circuit

symbol		dimensions			
		[mm]		[inch]	
		min	max	min	max
A	10.37	10.63	0.4084	0.4184	
B	15.86	16.12	0.6245	0.6345	
C	0.65	0.78	0.0256	0.0306	
D	2.95 typ.		0.1160 typ.		
E	3.15	3.25	0.124	0.128	
F	6.05	6.56	0.2384	0.2584	
G	13.47	13.73	0.5304	0.5404	
H	3.18	3.43	0.125	0.135	
K	0.45	0.63	0.0177	0.0247	
L	1.23	1.36	0.0484	0.0534	
M	2.54 typ.		0.100 typ.		
N	4.57	4.83	0.1800	0.1900	
P	2.57	2.83	0.1013	0.1113	
T	2.51	2.62	0.0990	0.1030	

Please refer to mounting instructions (application note AN-TO220-3-31-01)



symbol		dimensions			
		[mm]		[inch]	
		min	max	min	max
A	9.70	10.30	0.3819	0.4055	
B	14.88	15.95	0.5858	0.6280	
C	0.65	0.86	0.0256	0.0339	
D	3.55	3.89	0.1398	0.1531	
E	2.60	3.00	0.1024	0.1181	
F	6.00	6.80	0.2362	0.2677	
G	13.00	14.00	0.5118	0.5512	
H	4.35	4.75	0.1713	0.1870	
K	0.38	0.65	0.0150	0.0256	
L	0.95	1.32	0.0374	0.0520	
M	2.54 typ.		0.1 typ.		
N	4.30	4.50	0.1693	0.1772	
P	1.17	1.40	0.0461	0.0551	
T	2.30	2.72	0.0906	0.1071	



symbol	dimensions			
	[mm]		symbol	
	min		min	
A	6.40	A	6.40	A
B	5.25	B	5.25	B
C	(0.65)	C	(0.65)	C
D	0.63	D	0.63	D
E	2.28		E	
F	2.19	F	2.19	F
G	0.76	G	0.76	G
H	0.90	H	0.90	H
K	5.97	K	5.97	K
L	9.40	L	9.40	L
M	0.46	M	0.46	M
N	0.87	N	0.87	N
P	0.51	P	0.51	P
R	5.00	R	5.00	R
S	4.17	S	4.17	S
T	0.26	T	0.26	T
U	-	U	-	U

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